

# HiPerFRED™ Epitaxial Diode

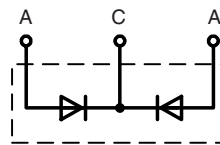
## with common cathode and soft recovery

$$I_{FAV} = 2 \times 30 \text{ A}$$

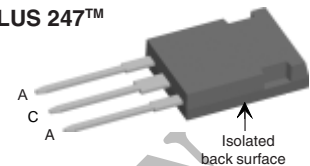
$$V_{RRM} = 300 \text{ V}$$

$$t_{rr} = 30 \text{ ns}$$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
300	300	DSEC 60-03AR



ISOPLUS 247™



A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings	
$I_{FRMS}$		70	A
$I_{FAVM}$	$T_C = 135^\circ\text{C}$ ; rectangular, $d = 0.5$	30	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sine	300	A
$E_{AS}$	$T_{VJ} = 25^\circ\text{C}$ ; non-repetitive $I_{AS} = 3 \text{ A}$ ; $L = 180 \mu\text{H}$	1.2	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_R$ typ.; $f = 10 \text{ kHz}$ ; repetitive	0.3	A
$T_{VJ}$		-55...+175	$^\circ\text{C}$
$T_{VJM}$		175	$^\circ\text{C}$
$T_{stg}$		-55...+150	$^\circ\text{C}$
$P_{tot}$	$T_C = 25^\circ\text{C}$	165	W
$F_C$	mounting force with clip	20...120	N
$V_{ISOL}$	50/60 Hz, RMS, $t = 1 \text{ minute}$ , leads-to-tab	2500	V~
Weight	typical	6	g

### Features

- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0
- Isolated and UL registered E153432

### Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{RM}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Dimensions see Outlines.pdf

Symbol	Conditions	Characteristic Values	
		typ.	max.
$I_R$ ①	$V_R = V_{RRM}$ ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$	10 1	$\mu\text{A}$ mA
$V_F$ ②	$I_F = 30 \text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	0.91 1.25	V V
$R_{thJC}$ $R_{thCH}$		0.25	K/W K/W
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-di/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	30	ns
$I_{RM}$	$V_R = 100 \text{ V}$ ; $I_F = 50 \text{ A}$ ; $-di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$	7	A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%

② Pulse Width = 300  $\mu\text{s}$ , Duty Cycle < 2.0%

Data according to IEC 60747 and per diode unless otherwise specified

**Recommended replacement:**  
**DPG 60C300HJ**

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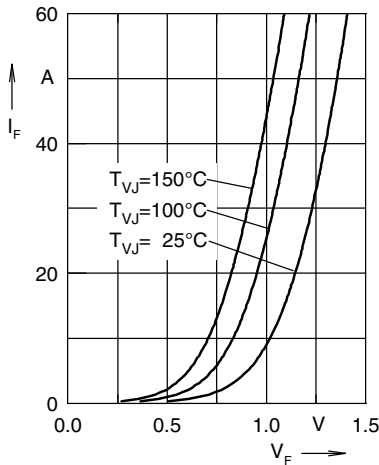


Fig. 1 Forward current  $I_F$  versus  $V_F$

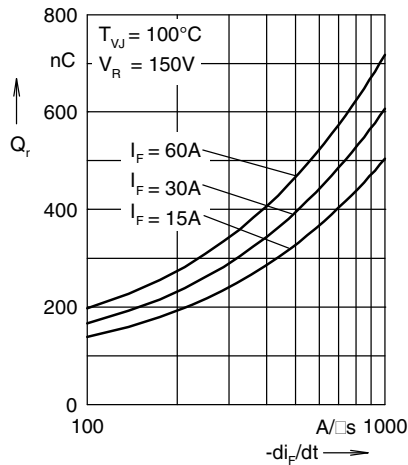


Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

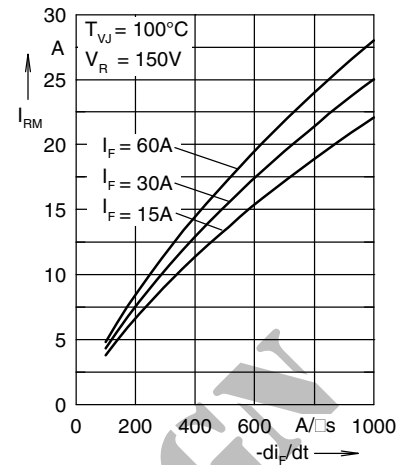


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

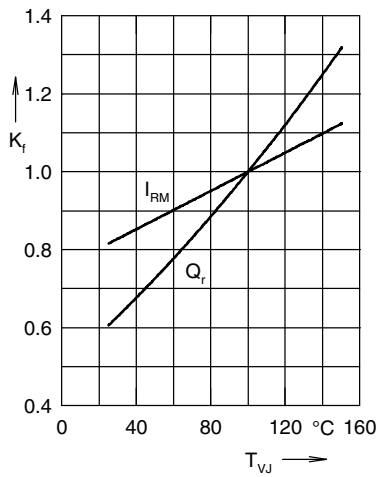


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

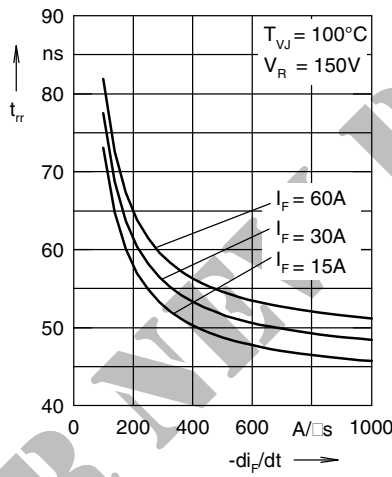


Fig. 5 Recovery time  $t_{rr}$  versus  $-di_F/dt$

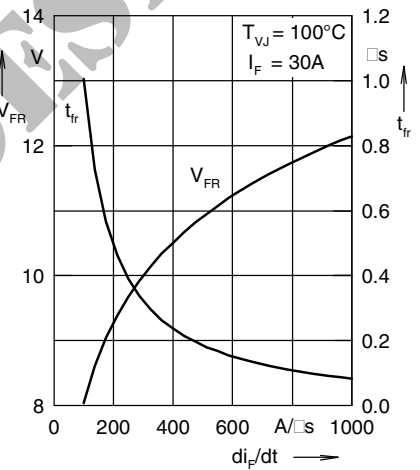


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

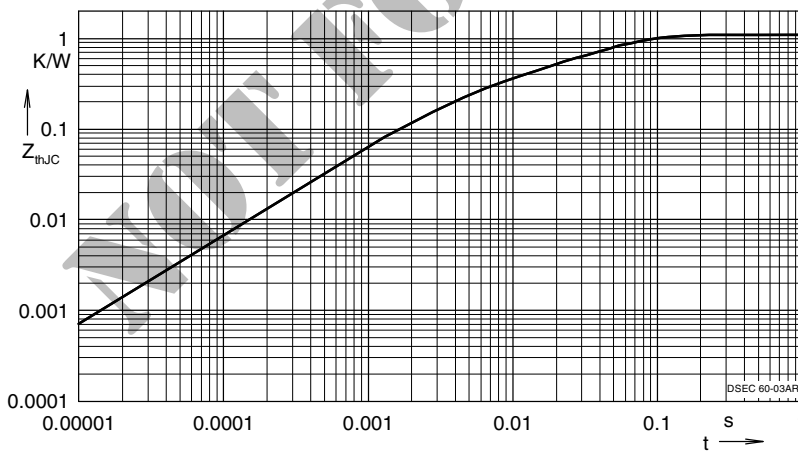


Fig. 7 Transient thermal resistance junction to case

Constants for  $Z_{thjC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.368	0.0052
2	0.1417	0.0003
3	0.0295	0.0004
4	0.5604	0.0092

NOTE: Fig. 2 to Fig. 6 shows typical values

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